

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
80V	4.5mΩ@10V	130A

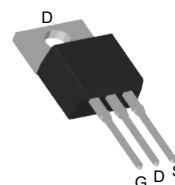
Feature

- Split Gate Trench Technology
- Low $R_{DS(on)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

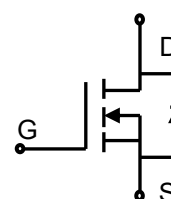
Application

- Power Switching Application
- Power Management
- BLDC Motor Drive Systems

TO-220-3L-C



Schematic diagram



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPT1933NTB	TO-220-3L-C	GPT1933	Tube	-	-	50pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	80	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current ¹	$T_C = 25^{\circ}\text{C}$	I_D	130	A
	$T_C = 100^{\circ}\text{C}$	I_D	92	A
Pulsed Drain Current ²		I_{DM}	520	A
Single Pulsed Avalanche Current ³		I_{AS}	42	A
Single Pulsed Avalanche Energy ³		E_{AS}	441	mJ
Power Dissipation ⁵	$T_C = 25^{\circ}\text{C}$	P_D	157	W
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	55	$^{\circ}\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	0.8	$^{\circ}\text{C/W}$
Junction Temperature		T_J	150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	80			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics ⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	2.6	4	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 50A$		4.5	7.0	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 40V, V_{GS} = 0V, f = 0.1MHz$		3449		pF
Output Capacitance	C_{oss}			681		
Reverse Transfer Capacitance	C_{rss}			27		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 40V, V_{GS} = 10V, I_D = 20A$		50		nC
Gate-source Charge	Q_{gs}			16		
Gate-drain Charge	Q_{gd}			11		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 40V, V_{GS} = 10V, I_D = 20A,$ $R_G = 3\Omega$		16		ns
Turn-on Rise Time	t_r			13		
Turn-off Delay Time	$t_{d(off)}$			32		
Turn-off Fall Time	t_f			14		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 50A$			1.2	V

Notes:

- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 80V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ C$.
- 4.Pulse Test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ C$. And device mounted on a large heatsink
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ C$.

Typical Characteristics

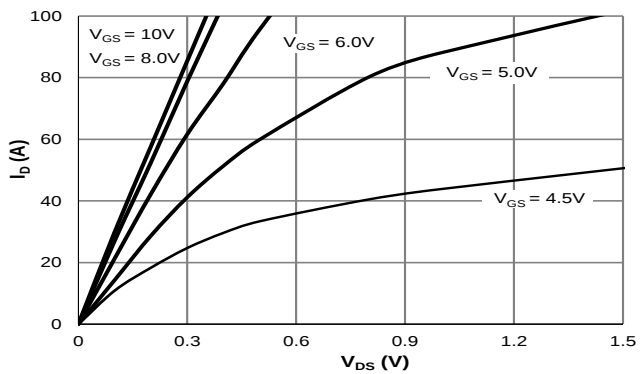


Figure 1: Saturation Characteristics

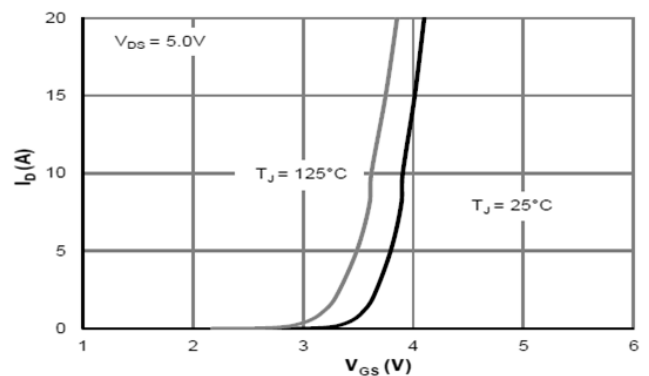


Figure 2: Transfer Characteristics

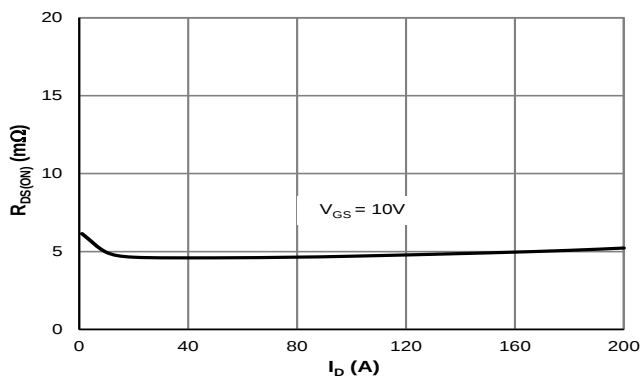


Figure 3: $R_{DS(ON)}$ vs. Drain Current

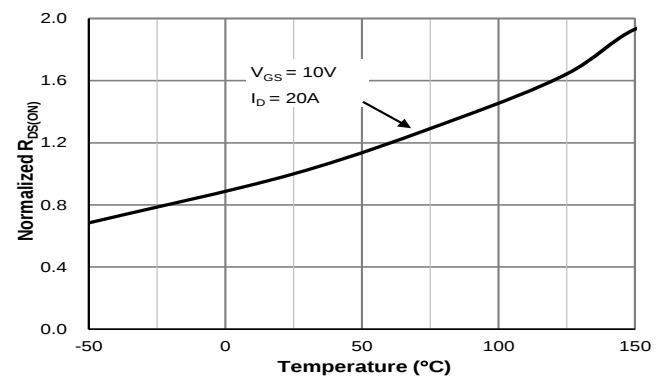


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

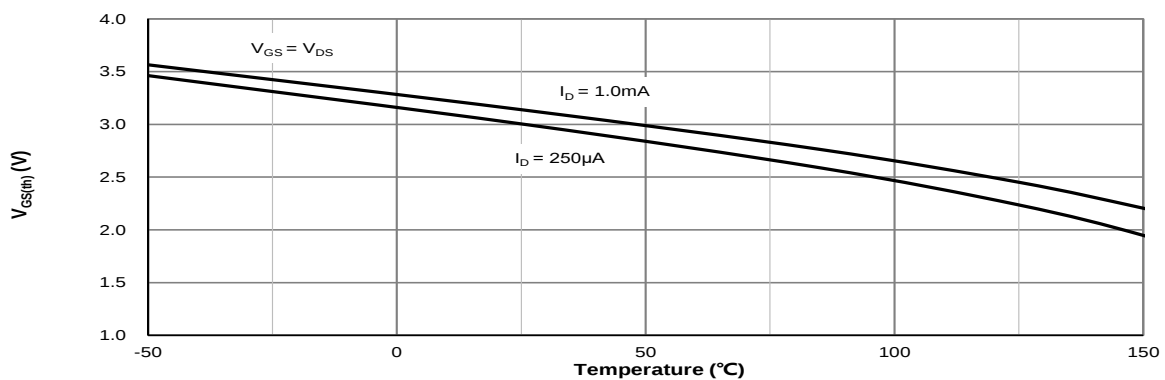


Figure 5: $V_{GS(th)}$ vs. Junction Temperature

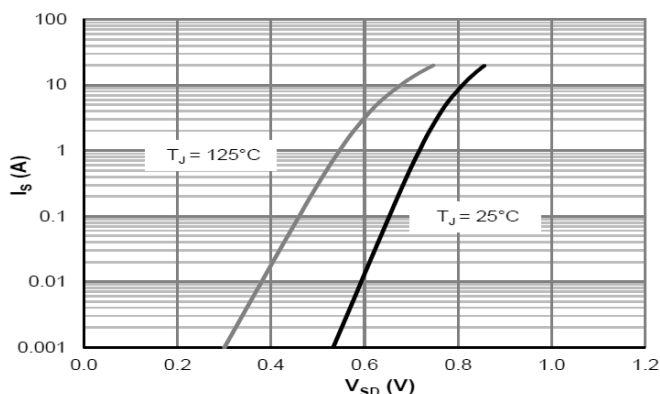


Figure 7: Body-Diode Characteristics

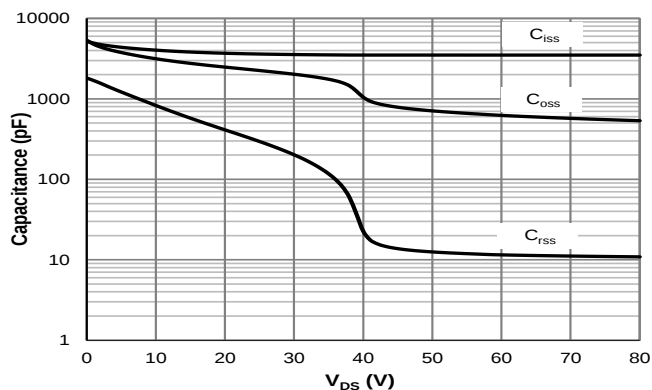


Figure 8: Capacitance Characteristics

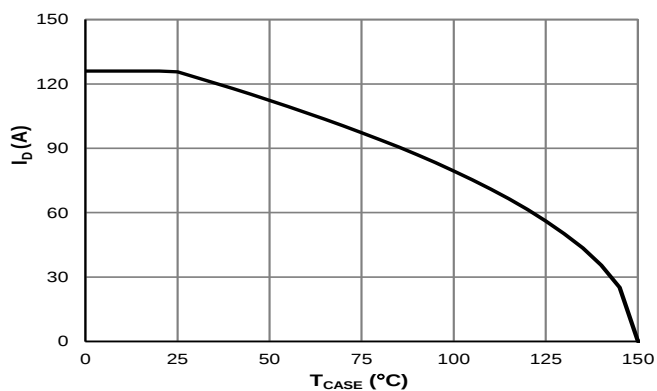


Figure 9: Current De-rating

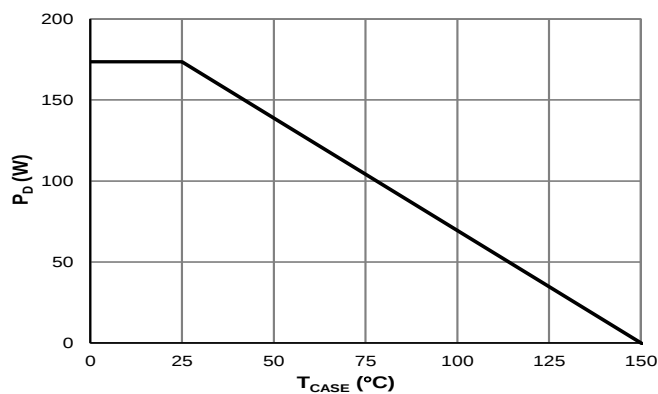


Figure 10: Power De-rating

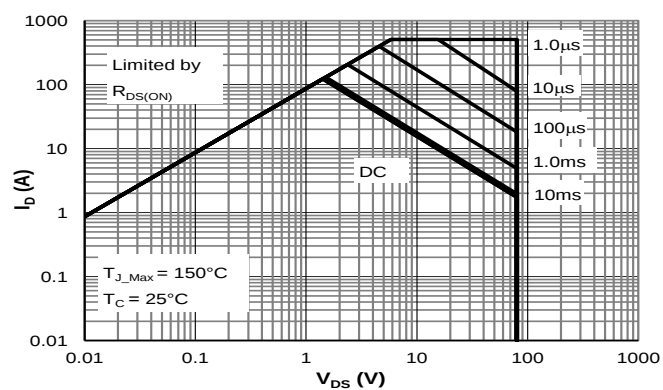


Figure 11: Maximum Safe Operating Area

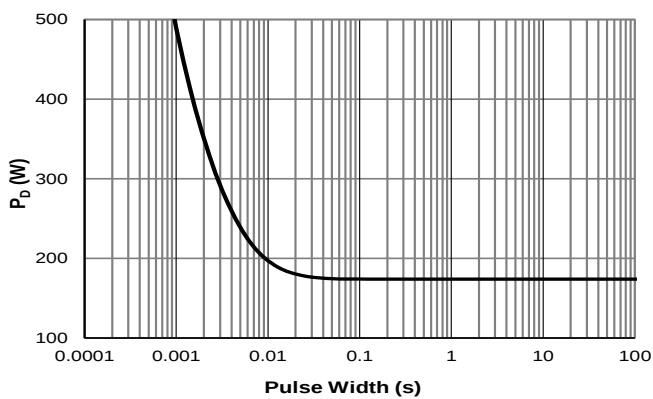


Figure 12: Single Pulse Power Rating, Junction-to-Case

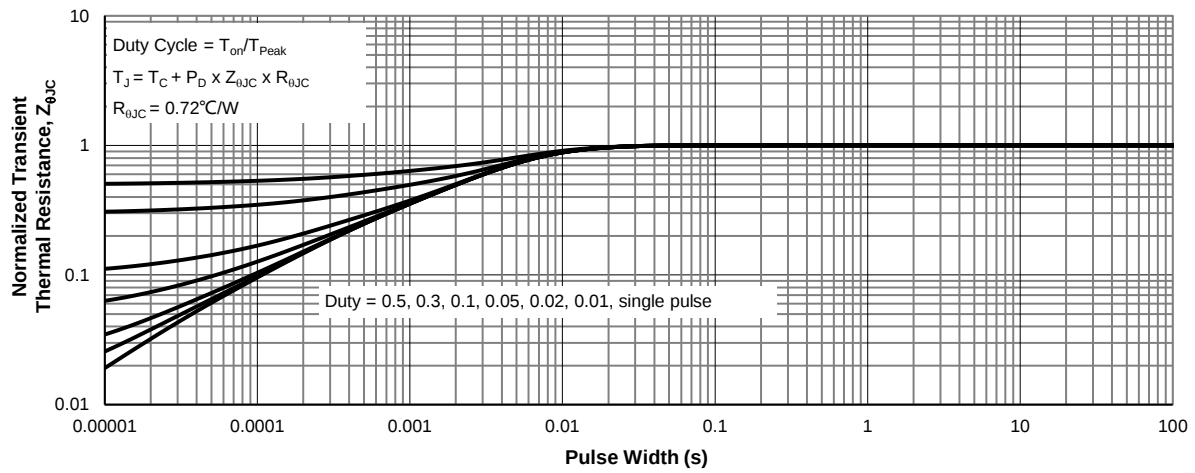
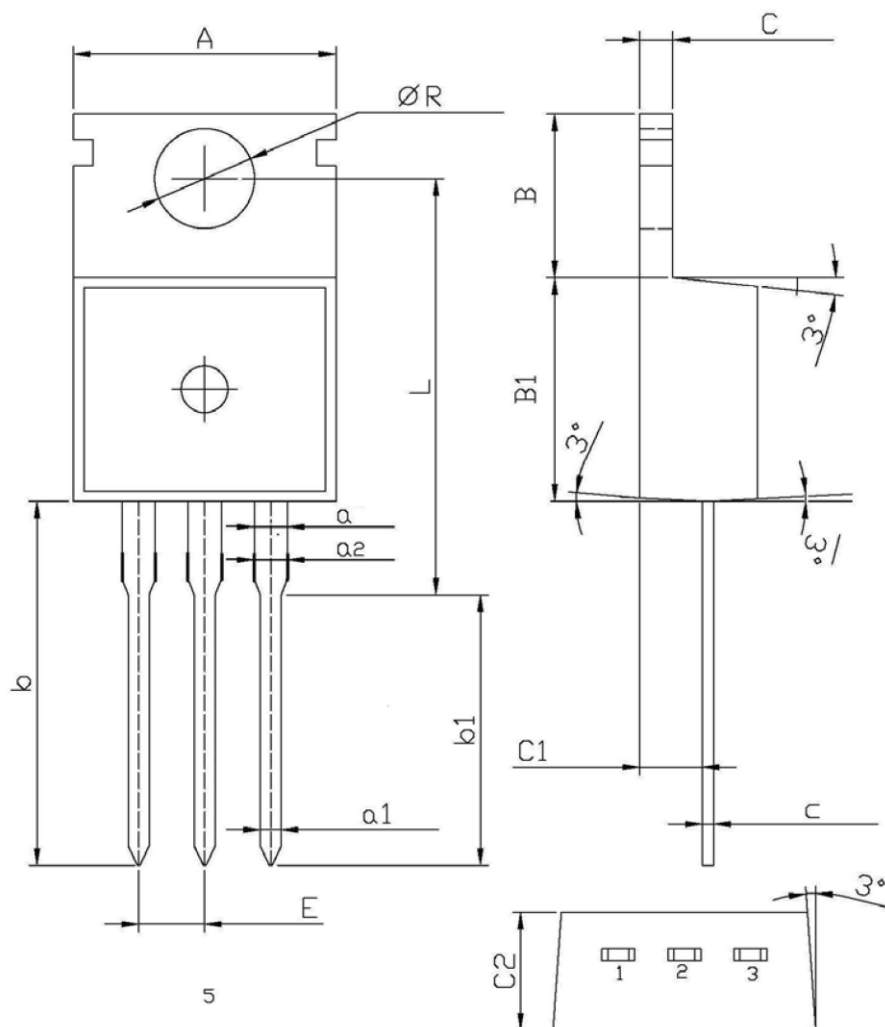


Figure 13: Normalized Maximum Transient Thermal Impedance

TO-220-3L-C Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	9.800	10.200	0.386	0.402
R	3.560	3.640	0.140	0.143
L	15.700	16.100	0.618	0.634
b	12.600	13.600	0.496	0.535
b1	9.600	10.600	0.378	0.417
a	1.220	1.320	0.048	0.052
E	2.340	2.740	0.092	0.108
a2	1.250	1.620	0.049	0.064
C	1.200	1.400	0.047	0.055
B	5.900	6.700	0.232	0.264
B1	9.000	9.400	0.354	0.370
C1	2.200	2.600	0.087	0.102
a1	0.700	0.900	0.028	0.035
c	0.400	0.600	0.016	0.024
C2	4.300	4.700	0.169	0.185

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.